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November 2013

FCP22N60N / FCPF22N60NT

N-Channel SupreMOS® MOSFET

600 V, 22 A, 165 mΩ

Features

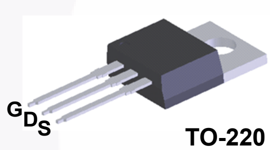
- BV_{DSS} > 650 V @ T_J = 150°C
- $R_{DS(on)}$ = 140 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 11 A
- Ultra Low Gate Charge (Typ. Q_g = 45 nC)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 196.4 pF)
- 100% Avalanche Tested
- RoHS Compliant

Application

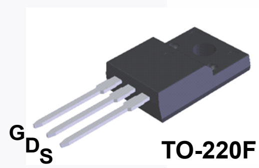
- LCD/LED/PDP TV
- Lighting
- Solar Inverter
- AC-DC Power Supply

Description

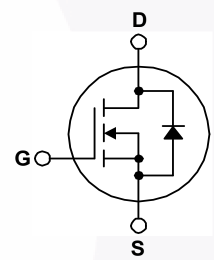
The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest Rsp on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.



TO-220



TO-220F



Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FCP22N60N	FCPF22N60NT	Unit
V_{DSS}	Drain to Source Voltage		600		V
V_{GSS}	Gate to Source Voltage		±45		V
I_D	Drain Current	- Continuous (T_C = 25°C)	22	22*	A
		- Continuous (T_C = 100°C)	13.8	13.8*	
I_{DM}	Drain Current	- Pulsed (Note 1)	66	66*	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		672		mJ
I_{AR}	Avalanche Current (Note 1)		7.3		A
E_{AR}	Repetitive Avalanche Energy (Note 1)		2.75		mJ
dv/dt	MOSFET dv/dt		100		V/ns
	Peak Diode Recovery dv/dt (Note 3)		20		
P_D	Power Dissipation	(T_C = 25°C)	205	39	W
		- Derate Above 25°C	1.64	0.31	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300		°C

*Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FCP22N60N	FCPF22N60NT	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.61	3.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCP22N60N	FCP22N60N	TO-220	Tube	N/A	N/A	50 units
FCPF22N60NT	FCPF22N60NT	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^oC$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit

Off Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0 V, $T_J = 25^oC$	600	-	-	V
		I_D = 1 mA, V_{GS} = 0 V, $T_J = 150^oC$	650	-	-	
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 1 mA, Referenced to 25^oC	-	0.68	-	$V/^oC$
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 480 V, V_{GS} = 0 V	-	-	10	μA
		V_{DS} = 480 V, $T_J = 125^oC$	-	-	100	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±45 V, V_{DS} = 0 V	-	-	±100	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, I_D = 250 μA	2.0	3.0	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 11 A	-	0.140	0.165	Ω
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 11 A	-	22	-	S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	V_{DS} = 100 V, V_{GS} = 0 V, f = 1 MHz	-	1950	-	pF
C_{oss}	Output Capacitance		-	75.9	-	pF
C_{rss}	Reverse Transfer Capacitance		-	3	-	pF
C_{oss}	Output Capacitance	V_{DS} = 380 V, V_{GS} = 0 V, f = 1 MHz	-	43.2	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	V_{DS} = 0 V to 480 V, V_{GS} = 0 V	-	196.4	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 380 V, I_D = 11 A, V_{GS} = 10 V (Note 4)	-	45	-	nC
Q_{gs}	Gate to Source Gate Charge		-	8.7	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	14.5	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-	1	-	Ω

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 380 V, I_D = 11 A, V_{GS} = 10 V, R_G = 4.7 Ω (Note 4)	-	16.9	-	ns
t_r	Turn-On Rise Time		-	16.7	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	49	-	ns
t_f	Turn-Off Fall Time		-	4	-	ns

Drain-Source Diode Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	22	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	66	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 11 A	-	-	1.2	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_{SD} = 11 A, dI_F/dt = 100 A/μs	-	350	-	ns
Q_{rr}	Reverse Recovery Charge		-	6	-	μC

Notes:
1. Repetitive rating: pulse width-limited by maximum junction temperature.
2. I_{AS} = 7.3 A, R_G = 25 Ω, starting T_J = 25°C.
3. $I_{SD} \le 22$ A, di/dt ≤ 200 A/μs, $V_{DD} \le 380$ V, starting T_J = 25°C.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

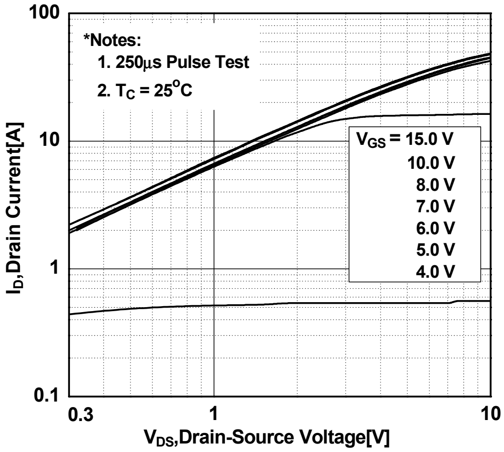


Figure 2. Transfer Characteristics

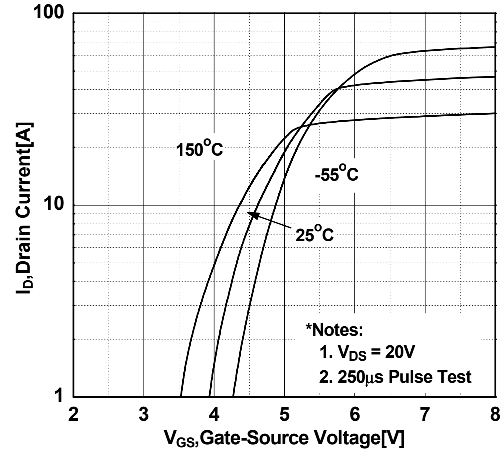


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

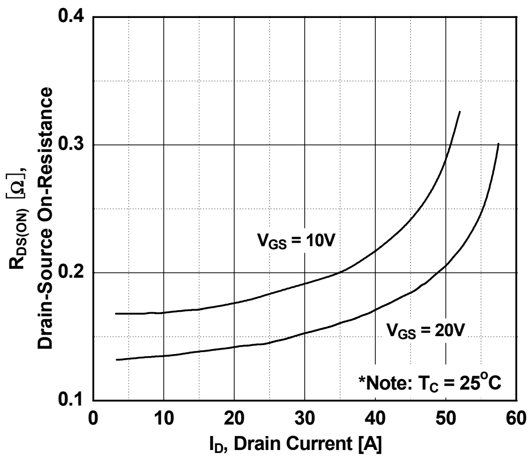


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

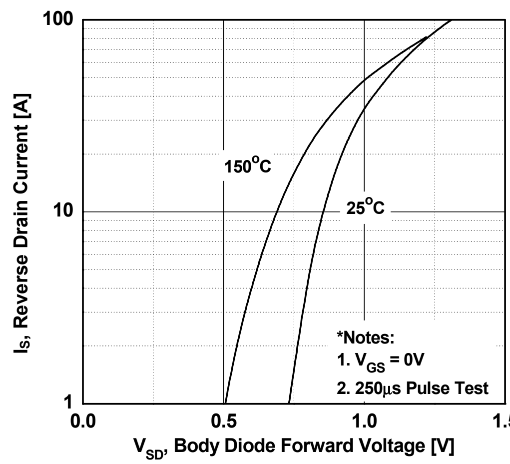


Figure 5. Capacitance Characteristics

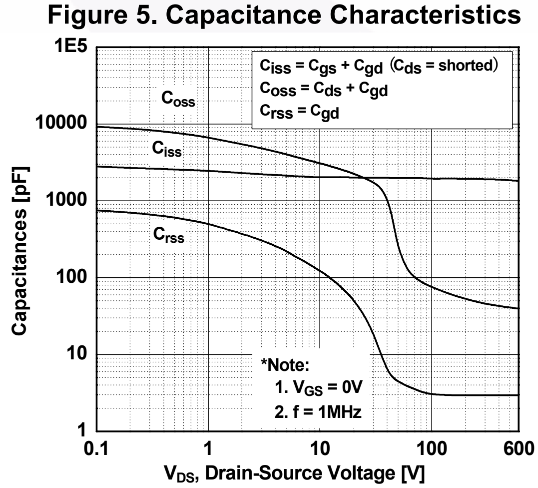
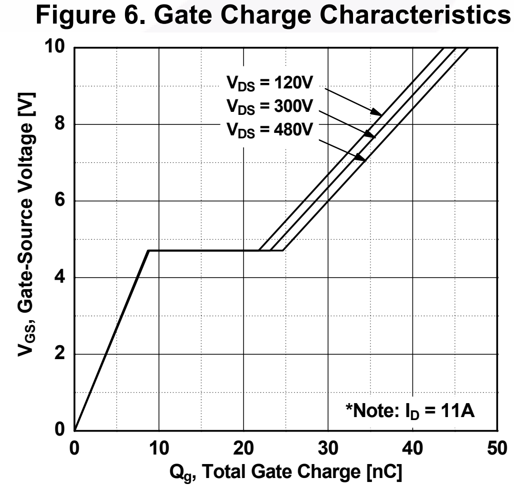


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

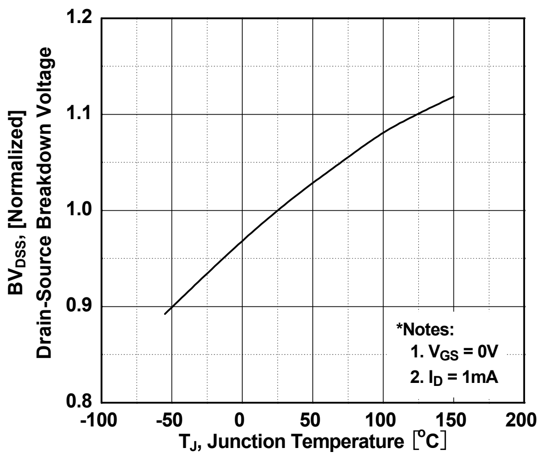


Figure 8. On-Resistance Variation vs. Temperature

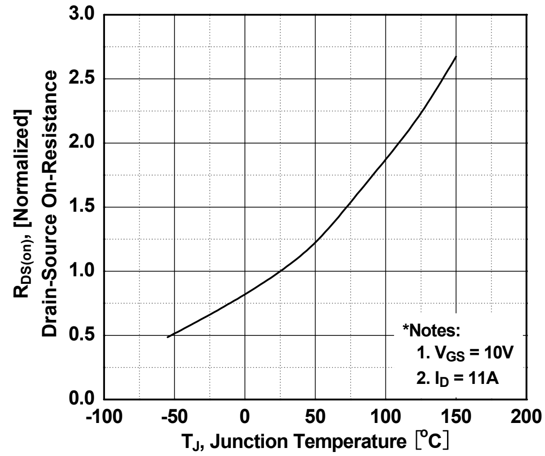


Figure 9. Maximum Safe Operating Area for FCP22N60N

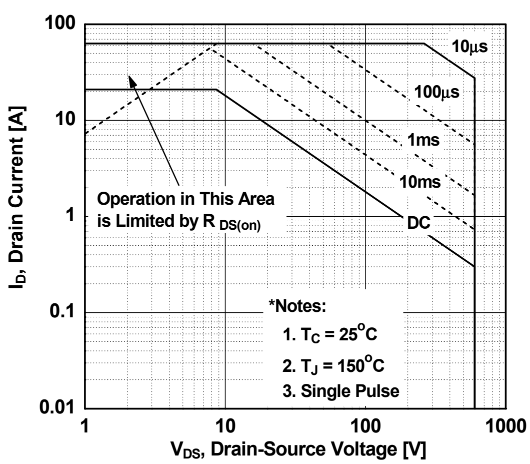


Figure 10. Maximum Safe Operating Area for FCPF22N60NT

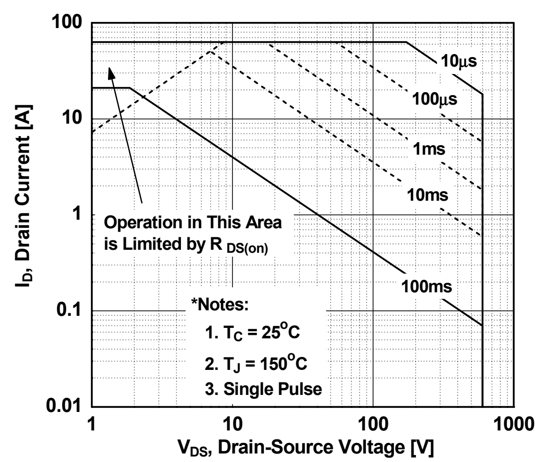
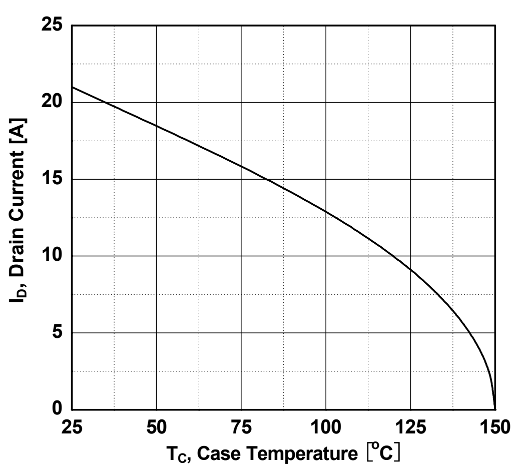


Figure 11. Maximum Drain Current vs.Case Temperature



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve for FCP22N60N

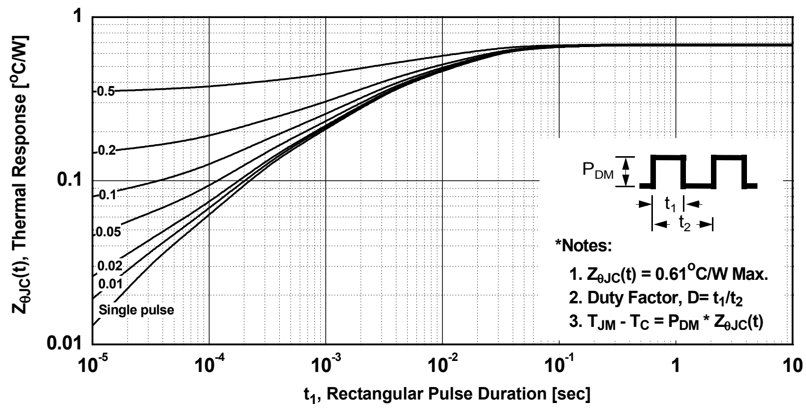
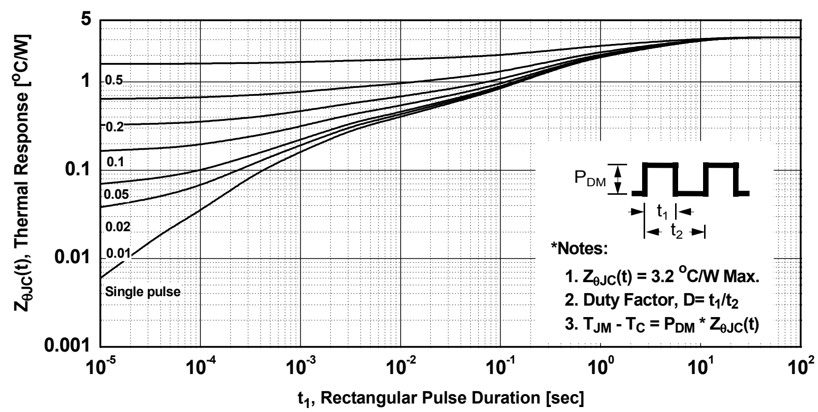


Figure 13. Transient Thermal Response Curve for FCPF22N60NT



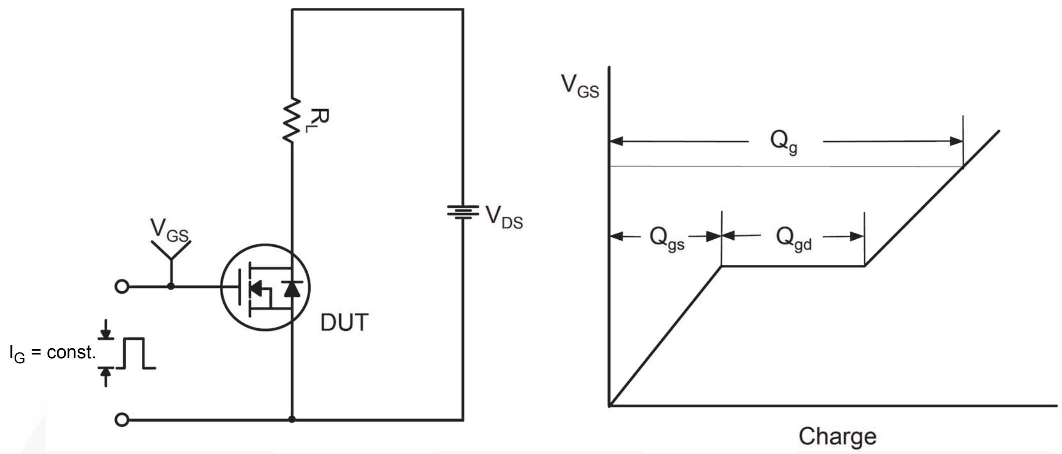


Figure 14. Gate Charge Test Circuit & Waveform

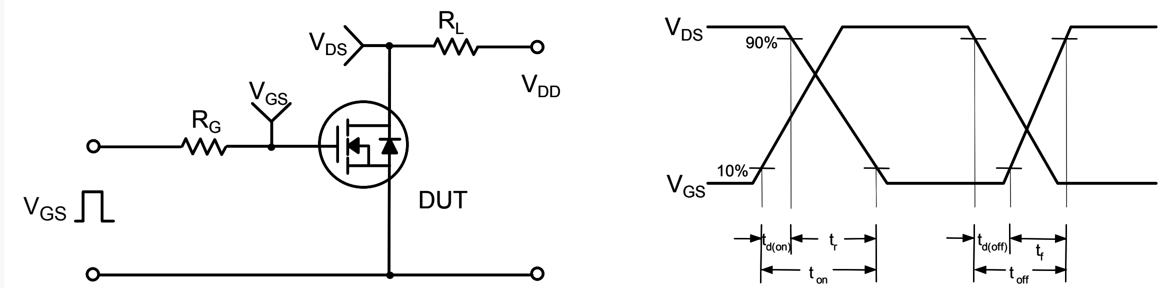


Figure 15. Resistive Switching Test Circuit & Waveforms

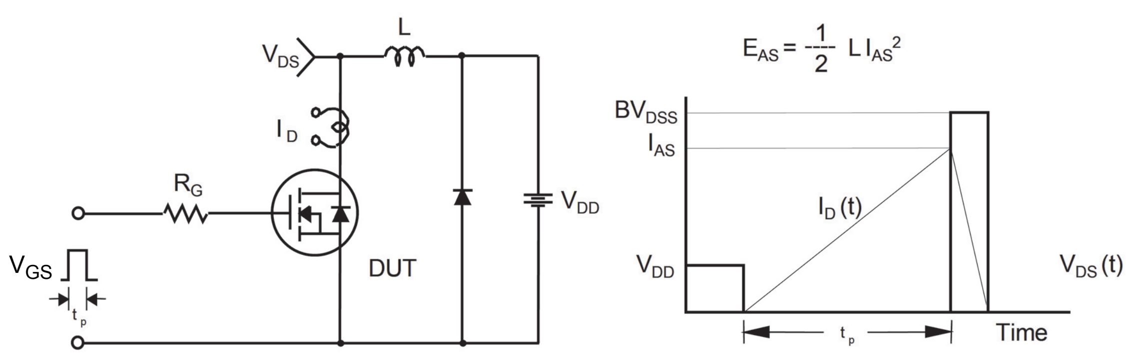


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

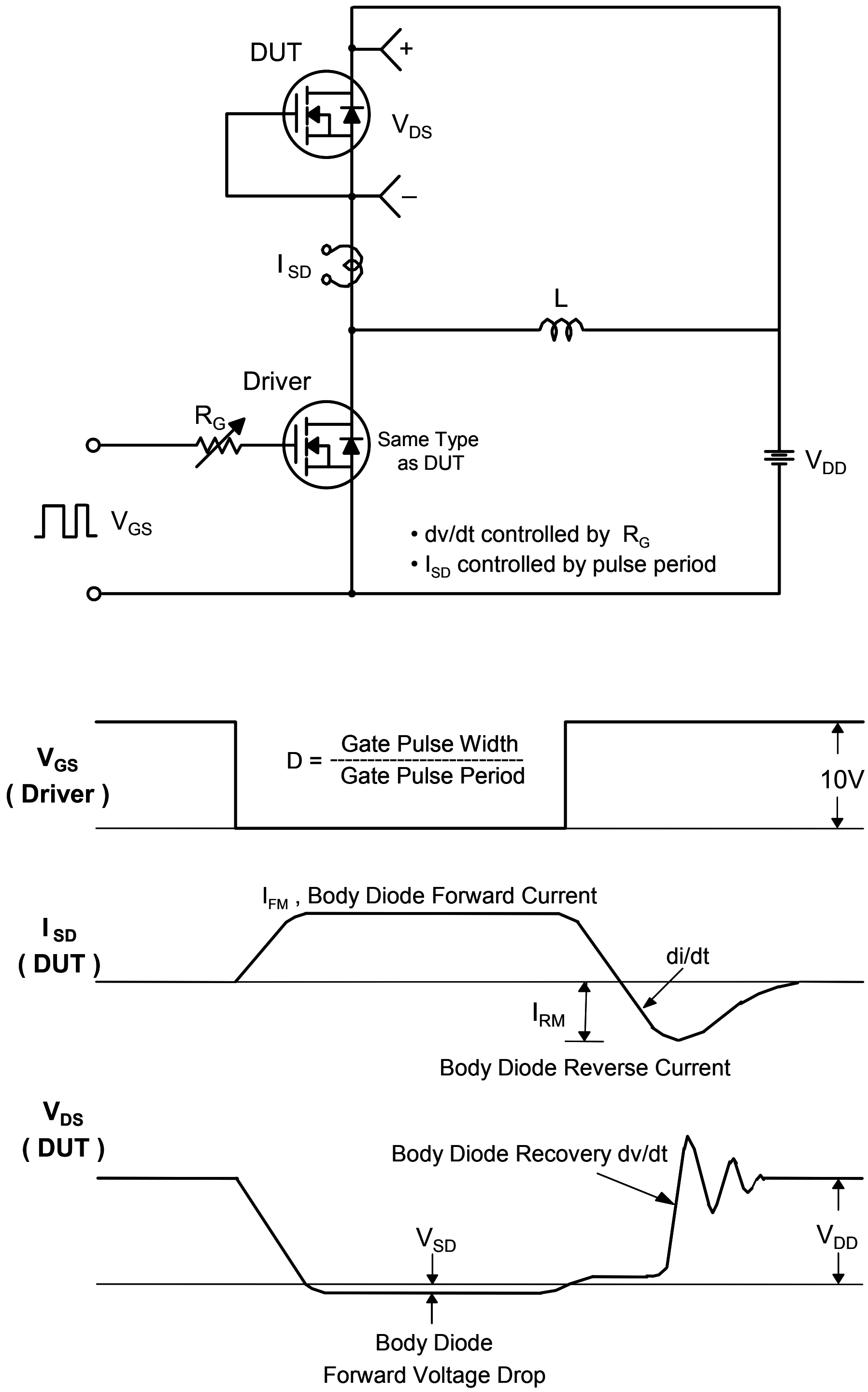


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

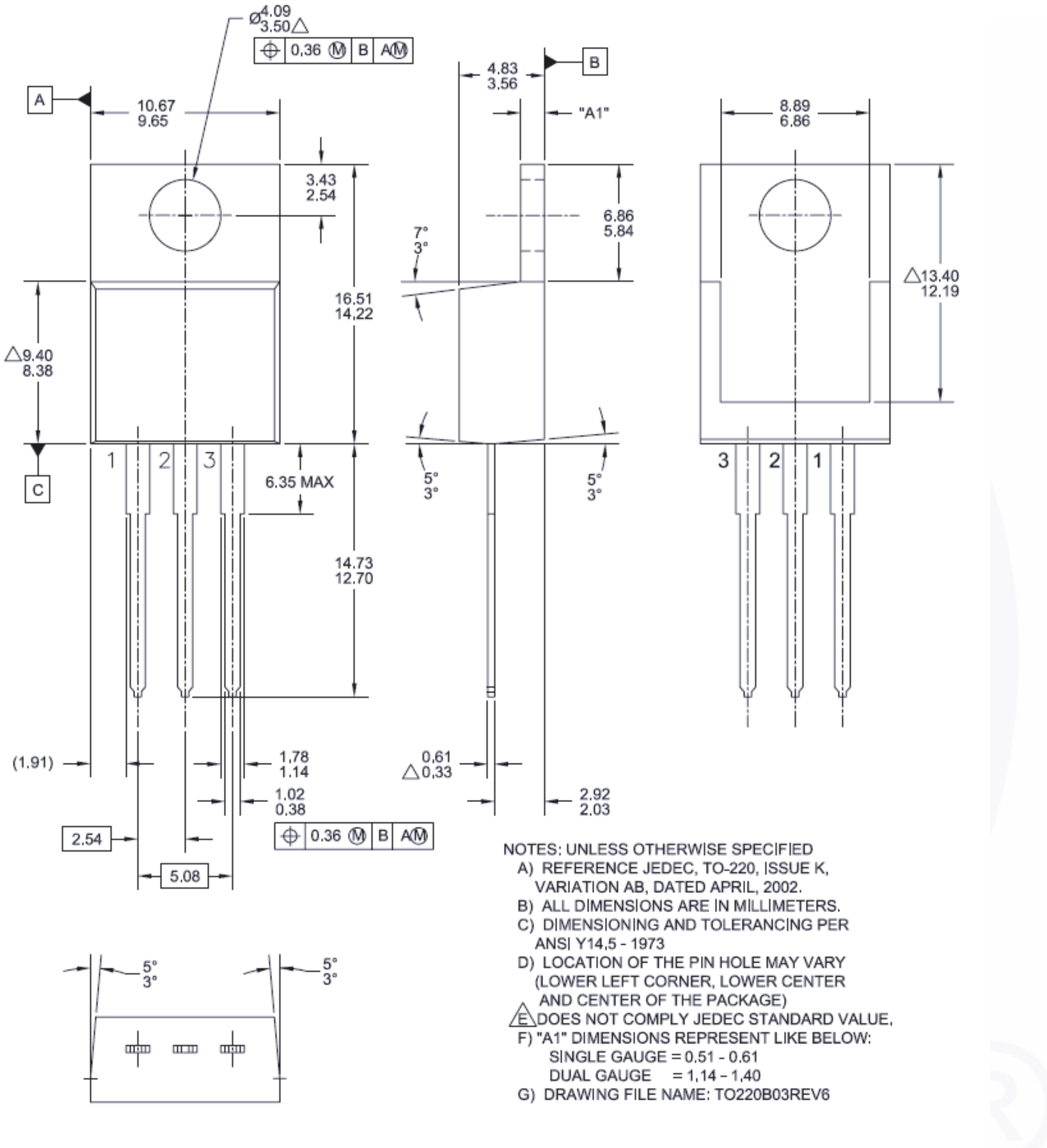


Figure 18. TO-220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

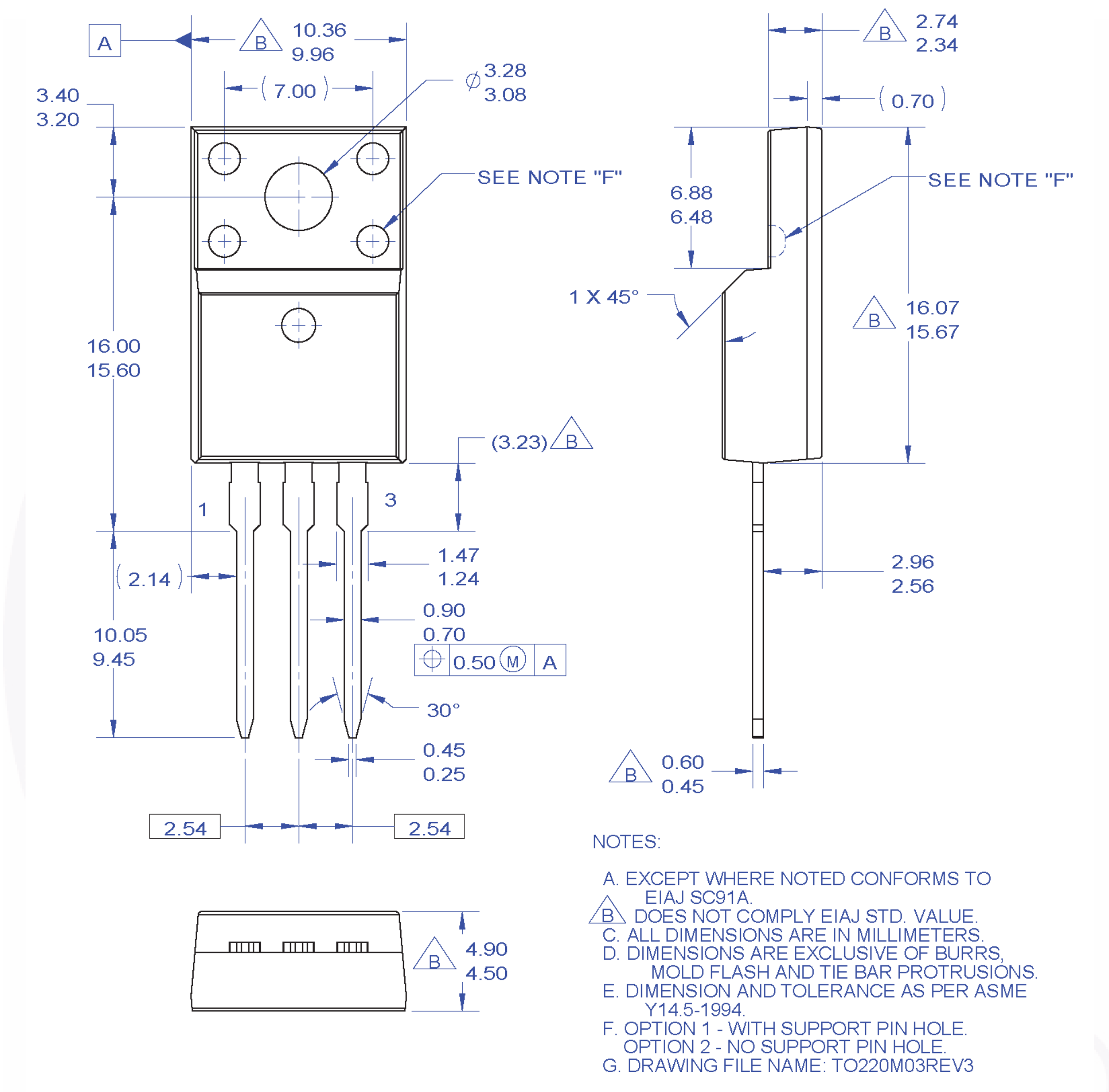

Figure 19. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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